

# Way Foong Lim

## List of Publications by Year in descending order

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papers

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docs citations

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times ranked

628  
citing authors

#	ARTICLE	IF	CITATIONS
1	Effects of Postdeposition Annealing in Argon Ambient on Metallorganic Decomposed CeO <sub>2</sub> Gate Spin Coated on Silicon. Journal of the Electrochemical Society, 2010, 157, H6.	2.9	61
2	Effects of CNTs content and milling time on mechanical behavior of MWCNT-reinforced aluminum nanocomposites. Materials Chemistry and Physics, 2015, 166, 160-166.	4.0	56
3	Comparison of metal-organic decomposed (MOD) cerium oxide (CeO <sub>2</sub> ) gate deposited on GaN and SiC substrates. Journal of Crystal Growth, 2011, 326, 2-8.	1.5	37
4	Investigation on structural and optical properties of SLS ZnO glasses prepared using a conventional melt quenching technique. Journal of Materials Science: Materials in Electronics, 2015, 26, 3722-3729.	2.2	35
5	Effect of Sintering Temperature on Structural and Morphological Properties of Europium (III) Oxide Doped Willemite. Journal of Spectroscopy, 2014, 2014, 1-8.	1.3	34
6	Electrical Properties of Pulsed Laser Deposited Y <sub>2</sub> O <sub>3</sub> Gate Oxide on 4H-SiC. Electrochemical and Solid-State Letters, 2010, 13, H396.	2.2	33
7	Oxygen vacancy formation and annihilation in lanthanum cerium oxide as a metal reactive oxide on 4H-silicon carbide. Physical Chemistry Chemical Physics, 2014, 16, 7015.	2.8	30
8	Effects of ammonia-ambient annealing on physical and electrical characteristics of rare earth CeO <sub>2</sub> as passivation film on silicon. Journal of Alloys and Compounds, 2017, 695, 3104-3115.	5.5	27
9	Physical characterization of post-deposition annealed metal-organic decomposed cerium oxide film spin-coated on 4H-silicon carbide. Journal of Alloys and Compounds, 2010, 497, 195-200.	5.5	26
10	Physical and electrical characteristics of metal-organic decomposed CeO <sub>2</sub> gate spin-coated on 4H-SiC. Applied Physics A: Materials Science and Processing, 2011, 103, 1067-1075.	2.3	26
11	Effects of post-deposition annealing temperature and time on physical properties of metal-organic decomposed lanthanum cerium oxide thin film. Thin Solid Films, 2011, 519, 5139-5145.	1.8	24
12	Fabrication and characterization of electrospun ZnO nanofibers; antimicrobial assessment. Materials Letters, 2020, 264, 127279.	2.6	24
13	Structural and Chemical Studies of Metal-Organic Decomposed La <sub>x</sub> Ce <sub>1-x</sub> O <sub>z</sub> Thin Film as a Catalytic Oxide on 4H-SiC as a Function of Postdeposition Annealing Time. Journal of Physical Chemistry C, 2013, 117, 14014-14024.	3.1	22
14	Alteration of structural and optical properties in quaternary Al <sub>0.1</sub> In <sub>0.1</sub> Ga <sub>0.8</sub> N films using ultraviolet assisted photo-electrochemical etching route. Journal of Alloys and Compounds, 2015, 649, 337-347.	5.5	22
15	Metal-oxide-semiconductor characteristics of lanthanum cerium oxide film on Si. Applied Physics A: Materials Science and Processing, 2012, 107, 459-467.	2.3	21
16	Influence of post-deposition annealing in oxygen ambient on metal-organic decomposed CeO <sub>2</sub> film spin coated on 4H-SiC. Journal of Materials Science: Materials in Electronics, 2012, 23, 257-266.	2.2	21
17	Effects of Post-Deposition Annealing on CeO <sub>2</sub> Gate Prepared by Metal-Organic Decomposition (MOD) Method on 4H-SiC. Materials Science Forum, 0, 645-648, 837-840.	0.3	20
18	Study of molar ratio on the characteristics of metal-organic decomposed La <sub>x</sub> Ce <sub>1-x</sub> O <sub>z</sub> film as a metal reactive oxide on Si substrate. Journal of Alloys and Compounds, 2013, 581, 793-800.	5.5	19

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19	Effects of post-deposition annealing temperature on metal-organic decomposed lanthanum cerium oxide film as metal reactive oxide layer on 4H-SiC. <i>Materials Chemistry and Physics</i> , 2013, 140, 622-633.	4.0	17
20	Characterization of Waste Material Derived Willemite-Based Glass-Ceramics Doped with Erbium. <i>Advances in Materials Science and Engineering</i> , 2015, 2015, 1-7.	1.8	17
21	Effects of Calcination on the Crystallography and Nonbiogenic Aragonite Formation of Ark Clam Shell under Ambient Condition. <i>Advances in Materials Science and Engineering</i> , 2016, 2016, 1-8.	1.8	17
22	An elucidating study on physical and structural properties of 45S5 glass at different sintering temperatures. <i>Journal of Non-Crystalline Solids</i> , 2015, 412, 24-29.	3.1	16
23	Passivation of silicon substrate using two-step grown ternary aluminium doped zirconium oxide. <i>Applied Surface Science</i> , 2019, 493, 411-422.	6.1	16
24	Investigation of Aloe Vera as active layer for development of organic based memory devices. <i>Materials Technology</i> , 2015, 30, A29-A35.	3.0	15
25	A two-step growth route of ternary aluminium doped zirconium oxide film on silicon. <i>Journal of Alloys and Compounds</i> , 2019, 777, 736-748.	5.5	14
26	Manganese modified structural and optical properties of zinc soda lime silica glasses. <i>Applied Optics</i> , 2016, 55, 2182.	2.1	13
27	Effects of ultraviolet-assisted electrochemical etching current densities on structural and optical characteristics of porous quaternary AlInGaN alloys. <i>Arabian Journal of Chemistry</i> , 2019, 12, 3417-3430.	4.9	13
28	Wet oxidation growth of hafnium doped tantalum oxide films with different composition deposited on silicon substrate. <i>Applied Surface Science</i> , 2020, 526, 146722.	6.1	12
29	Porous Formation in p-Type Gallium Nitride Films via 50ÅHz Operated Alternating Current-Assisted Photo-Electrochemical Etching in Methanol-Sulfuric Acid Solution. <i>Journal of the Electrochemical Society</i> , 2018, 165, H620-H628.	2.9	11
30	Surface Alteration of Planar P-Type Gallium Nitride to Porous Structure Using 50 Hz Alternating Current-Assisted Photo-Electrochemical Etching Route. <i>Journal of the Electrochemical Society</i> , 2016, 163, H642-H651.	2.9	10
31	Effects of annealing temperature on optical, morphological, and electrical characteristics of polyfluorene-derivative thin films on ITO glass substrate. <i>Applied Optics</i> , 2016, 55, 1198.	2.1	10
32	Structural and optical investigation of porous quaternary Al <sub>0.10</sub> In <sub>0.10</sub> Ga <sub>0.80</sub> N films produced via ultraviolet-assisted photo-electrochemical etching in acidic solutions. <i>Journal of Alloys and Compounds</i> , 2016, 662, 32-43.	5.5	9
33	Structural, morphological, optical, and gas sensing characteristics of ultraviolet-assisted photoelectrochemical etching derived AlInGaN nano-spikes. <i>Journal of Materials Research and Technology</i> , 2019, 8, 2767-2776.	5.8	9
34	Porous Quaternary Al <sub>0.1</sub> In <sub>0.1</sub> Ga <sub>0.8</sub> N Film Formation via Photoelectrochemical Etching in HF:C <sub>2</sub> H <sub>5</sub> OH Electrolyte. <i>Journal of the American Ceramic Society</i> , 2016, 99, 2395-2401.	3.8	8
35	Effects of rapid thermal annealing on structural, chemical, and electrical characteristics of atomic-layer deposited lanthanum doped zirconium dioxide thin film on 4H-SiC substrate. <i>Applied Surface Science</i> , 2016, 365, 296-305.	6.1	8
36	Influence of post-deposition annealing on metal-organic decomposed lanthanum cerium oxide film. , 2011, , .		7

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37	Effect of annealing temperature on physical and electrical properties of solution-processed polycrystalline In <sub>2</sub> Ga <sub>2</sub> ZnO <sub>7</sub> thin film. <i>Journal of Materials Science: Materials in Electronics</i> , 2020, 31, 9705-9718.	2.2	7
38	Effect of microwave time on the structural and luminescence properties of YAG:Ce prepared by microwave solution combustion (MSC) synthesis. <i>Optik</i> , 2020, 212, 164437.	2.9	7
39	Formation of cerium oxide film via post-sputter oxidation of cerium in nitrogen/oxygen/nitrogen ambient. <i>Journal of Alloys and Compounds</i> , 2021, 851, 156786.	5.5	7
40	Dual-step grown ternary aluminium zirconium oxide and its characteristics for metal-oxide-semiconductor capacitor. <i>Ceramics International</i> , 2020, 46, 10416-10424.	4.8	6
41	Effects of Post-Deposition Annealing Temperature on Band Alignment and Electrical Characteristics of Lanthanum Cerium Oxide on 4H-SiC. <i>Materials Research Society Symposia Proceedings</i> , 2012, 1433, 7.	0.1	5
42	Investigation on structural, morphological, optical, and current-voltage characteristics of polyfluorene with dissimilar composition spin coated on ITO. <i>Optik</i> , 2021, 242, 167034.	2.9	5
43	Characterization of Aging Behavior of AA6061 Aluminum Alloy Through Destructive and Ultrasonic Non-destructive Testing Techniques. <i>Transactions of the Indian Institute of Metals</i> , 2015, 68, 561-569.	1.5	4
44	Simultaneous two-step assisted growth of aluminium zirconium oxide from Al <sup>+</sup> Zr films. <i>Ceramics International</i> , 2020, 46, 297-306.	4.8	4
45	Ultralow Voltage Operation of $\{m\text{Al}\}/\{m\text{La}\}_{x}\{m\text{Ce}\}_{1-x}\{m\text{O}\}_{z}/\{m\text{4H}\}\{\text{-}\}\{\text{SiC}\}$ for Oxygen Sensing. <i>IEEE Electron Device Letters</i> , 2013, 34, 1430-1432.	3.9	3
46	Growth and Characterization of Ternary Hf <sub>x</sub> Ta <sub>y</sub> O <sub>z</sub> Films via Nitrogen-Infused Wet Oxidation. <i>ACS Omega</i> , 2020, 5, 26347-26356.	3.5	3
47	Comparative study of oxidizing ambient infused with varying nitrogen flow rates for fabrication of ternary nitrided AlZrO based MOS capacitor. <i>International Journal of Energy Research</i> , 2021, 45, 3838-3851.	4.5	3
48	Comparative studies of metal-organic decomposed Ga <sub>x</sub> Ce <sub>y</sub> O <sub>z</sub> and CeO <sub>2</sub> based functional MOS capacitor. <i>International Journal of Energy Research</i> , 2021, 45, 18257-18261.	4.5	3
49	Effects of V/III ratio of InGaN quantum well at high growth temperature for near ultraviolet light emitting diodes. <i>Microelectronics International</i> , 2021, 38, 119-126.	0.6	3
50	Analysis using a two-layer model of the transport properties of InGaN epilayers grown on GaN template substrate. <i>Materials Science in Semiconductor Processing</i> , 2022, 144, 106614.	4.0	3
51	Influence of post-deposition annealing time on oxygen gas sensing behaviour of Al <sub>0.50</sub> Ce <sub>0.50</sub> O <sub>1.75</sub> /Si metal-oxide-semiconductor capacitor. <i>Materials Research Innovations</i> , 2014, 18, S6-490-S6-494.	2.3	2
52	Room temperature hydrogen gas sensing characteristics of porous quaternary AlInGaN film prepared via UV-assisted photo-electrochemical etching. <i>Superlattices and Microstructures</i> , 2016, 95, 65-70.	3.1	2
53	Preparation and characterisation of aluminium zirconium oxide for metal-oxide-semiconductor capacitor. <i>International Journal of Energy Research</i> , 2020, 44, 10562-10575.	4.5	2
54	Exploratory studies on wet oxidation grown ternary hafnium tantalum oxide for metal-oxide-semiconductor application. <i>International Journal of Energy Research</i> , 2022, 46, 4699-4711.	4.5	2

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55	Effects of Post-Deposition Annealing Time on Metal-Organic Decomposed Lanthanum Cerium Oxide Film Spin-Coated on Si Substrate. <i>Advanced Materials Research</i> , 0, 1024, 364-367.	0.3	1
56	High temperature growth of aluminium doped zirconium oxide via post-sputter oxidation of Al <sup>3+</sup> Zr films with different composition. <i>Journal of Alloys and Compounds</i> , 2020, 813, 152206.	5.5	1
57	Effect of etching time onto structural, morphological, and optical characteristics of quaternary AlInGaN films on Si substrate. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2021, 263, 114911.	3.5	1
58	Tailoring In <sub>2</sub> Ga <sub>2</sub> ZnO <sub>7</sub> thin film properties by annealing time effect. <i>Materials Chemistry and Physics</i> , 2021, 262, 124281.	4.0	1
59	The role of growth temperature on the indium incorporation process for the MOCVD growth of InGaN/GaN heterostructures. <i>Microelectronics International</i> , 2021, 38, 105-112.	0.6	1
60	Synergetic effects of monoethanolamine (MEA) and post-deposition calcination on biosynthesized CeO <sub>2</sub> nanostructures spin-coated on silicon substrate. <i>Materials Chemistry and Physics</i> , 2022, 278, 125656.	4.0	1
61	Influence of post-deposition annealing on metal-organic decomposed lanthanum cerium oxide film. , 2012, , .		0
62	Effects of Post-Deposition Annealing Time in Forming Gas Ambient on Y <sub>2</sub> O <sub>3</sub> Films Deposited on Silicon Substrate. <i>Journal of Physics: Conference Series</i> , 2020, 1535, 012031.	0.4	0
63	High-k La <sub>x</sub> Ce <sub>y</sub> O <sub>z</sub> for Passivation of Si Substrate. <i>Journal of Physics: Conference Series</i> , 2020, 1535, 012030.	0.4	0
64	Surface passivation via two-step grown nitrogen infused oxidation derived quaternary Al <sub>x</sub> Zr <sub>1-x</sub> O <sub>y</sub> N <sub>z</sub> . <i>Materials Letters</i> , 2020, 276, 128175.	2.6	0
65	Effects of oxidation time on the formation of nanosized cerium oxide film from direct current sputtered cerium. <i>Emergent Materials</i> , 2022, 5, 41-49.	5.7	0